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Nanorelief formation under ion irradiation of silicon and germanium

The surface topography of silicon and germanium single crystals under irradiation by 3, 5 and 10 keV Ar⁺ and Ne⁺ ions was investigated. The relief of nanometer scale (so-called nanorelief) was revealed by atomic force microscopy. The silicon substrate doping level was found to be effect on nanorelief parameters. The obtained results are discussed in a frame of Harper-Bradly theory.